

Advanced Power MOSFET

IRFZ44

FEATURES

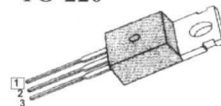
- ◆ Avalanche Rugged Technology
- ◆ Rugged Gate Oxide Technology
- ◆ Lower Input Capacitance
- ◆ Improved Gate Charge
- ◆ Extended Safe Operating Area
- ◆ 175°C Operating Temperature
- ◆ Lower Leakage Current: 10μA (Max.) @ $V_{DS} = 60V$
- ◆ Lower $R_{DS(ON)}$: 0.020Ω (Typ.)

$$BV_{DSS} = 60 V$$

$$R_{DS(on)} = 0.024\Omega$$

$$I_D = 50 A$$

TO-220



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current ($T_C=25^\circ C$)	50	A
	Continuous Drain Current ($T_C=100^\circ C$)	35.4	
I_{DM}	Drain Current-Pulsed (1)	200	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (2)	857	mJ
I_{AR}	Avalanche Current (1)	50	A
E_{AR}	Repetitive Avalanche Energy (1)	12.6	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	5.5	V/ns
P_D	Total Power Dissipation ($T_C=25^\circ C$)	126	W
	Linear Derating Factor	0.84	
T_J, T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +175	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.19	°C/W
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

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N-CHANNEL POWER MOSFET

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	60	--	--	V	$V_{GS}=0V, I_D=250\mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.063	--	V/ $^\circ\text{C}$	$I_D=250\mu\text{A}$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=5V, I_D=250\mu\text{A}$
I_{GSS}	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-20V$
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS}=60V$
		--	--	100		$V_{DS}=48V, T_C=150^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.024	Ω	$V_{GS}=10V, I_D=25A$ (4)
g_{fs}	Forward Transconductance	--	32.6	--	\bar{u}	$V_{DS}=30V, I_D=25A$ (4)
C_{iss}	Input Capacitance	--	1770	2300	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	--	590	680		
C_{rss}	Reverse Transfer Capacitance	--	220	255		
$t_{d(on)}$	Turn-On Delay Time	--	20	40	ns	$V_{DD}=30V, I_D=50A,$ $R_G=9.1\Omega$ See Fig 13 (4) (5)
t_r	Rise Time	--	16	40		
$t_{d(off)}$	Turn-Off Delay Time	--	68	140		
t_f	Fall Time	--	70	140		
Q_g	Total Gate Charge	--	64	83	nC	$V_{DS}=48V, V_{GS}=10V,$ $I_D=50A$ See Fig 6 & Fig 12 (4) (5)
Q_{gs}	Gate-Source Charge	--	12.3	--		
Q_{gd}	Gate-Drain (. Miller.) Charge	--	23.6	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	50	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current (1)	--	--	200		
V_{SD}	Diode Forward Voltage (4)	--	--	1.8	V	$T_J=25^\circ\text{C}, I_S=50A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	85	--	ns	$T_J=25^\circ\text{C}, I_F=50A$
Q_{rr}	Reverse Recovery Charge	--	0.24	--	μC	$di_F/dt=100A/\mu\text{s}$ (4)

Notes;

- (1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- (2) $L=0.4\text{mH}, I_{AS}=50A, V_{DD}=25V, R_G=27\Omega,$ Starting $T_J=25^\circ\text{C}$
- (3) $I_{SD} \leq 50A, di/dt \leq 350A/\mu\text{s}, V_{DD} \leq BV_{DSS},$ Starting $T_J=25^\circ\text{C}$
- (4) Pulse Test : Pulse Width = $250\mu\text{s},$ Duty Cycle $\leq 2\%$
- (5) Essentially Independent of Operating Temperature